

Fig. 1. Seven SIMS In depth profiles of In30K7.85E13 implant in Si, acquired with O^+_2 2KeV impacting energy, at 48eV energy slit and seven different voltage offsets from -10 to -30 eV.

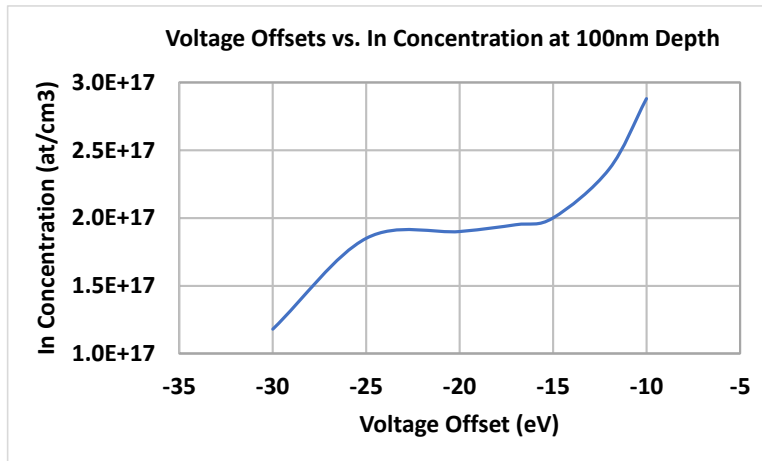


Fig. 2. In concentration level changes at 100nm depth vs. the voltage offset value variations from -10 to -30 eV.

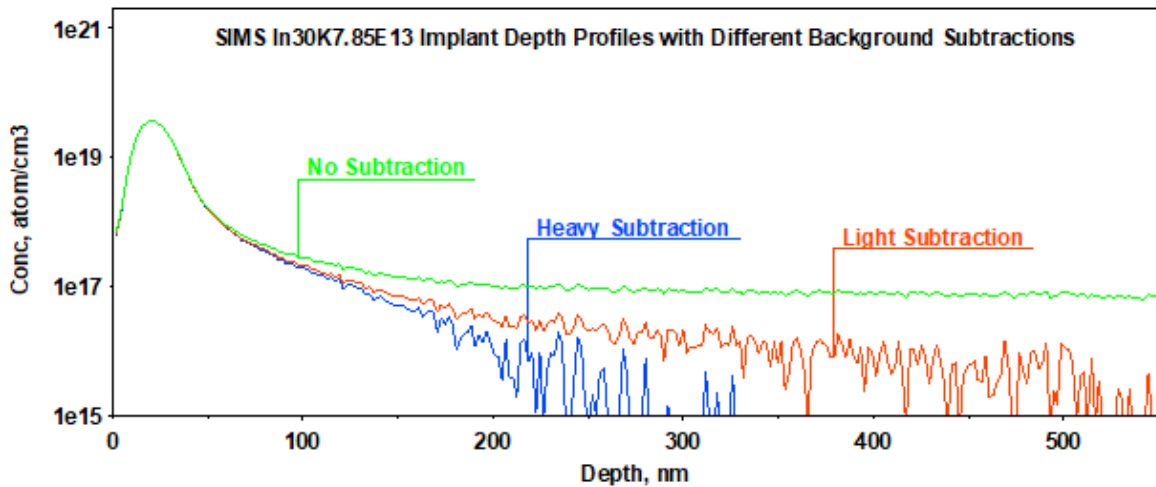


Fig. 3. Same SIMS In depth profiles of In30KeV7.85E13 implant in Si, no background subtraction and no voltage offset in green, light background subtraction in red, and heavy background subtraction in blue.

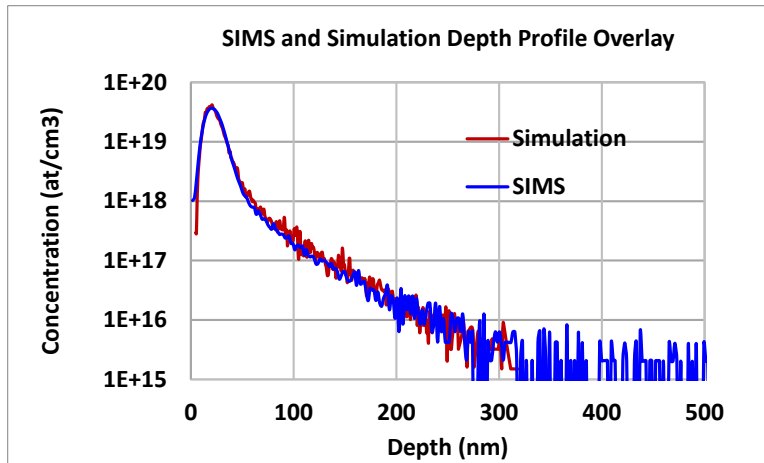


Fig. 4. SIMS and TCAD Montecarlo simulation depth profile overlay of In₃₀KeV7.85E13 implant in Si, with SIMS profile acquired at -17eV voltage offset, and no background subtraction.

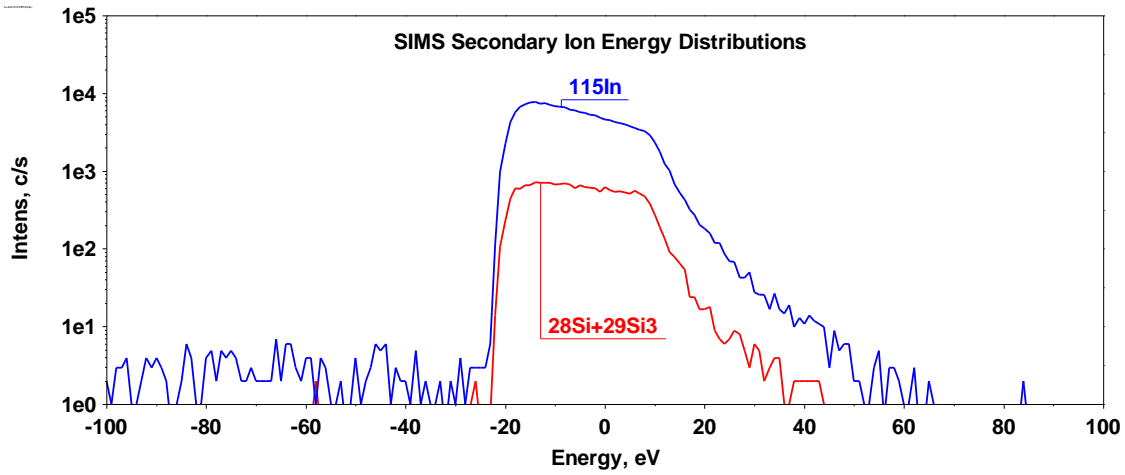


Fig. 5. SIMS ¹¹⁵In and ²⁸Si+²⁹Si₃ secondary ion distributions from -100 to +100eV.